

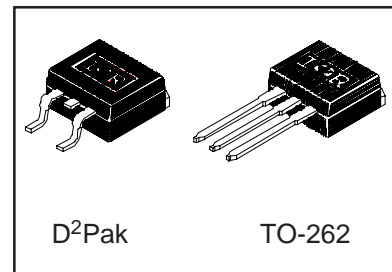
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptable Power Supply
- High Speed Power Switching

V_{DSS}	R_{DS(on)} max	I_D
500V	1.40Ω	5.0A

Benefits

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective Coss specified (See AN 1001)



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V ^⑥	5.0	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V ^⑥	3.2	
I _{DM}	Pulsed Drain Current ^① ⑥	20	
P _D @ T _A = 25°C	Power Dissipation	3.1	W
P _D @ T _C = 25°C	Power Dissipation	74	
	Linear Derating Factor	0.59	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ^③ ⑥	5.3	V/ns
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Typical SMPS Topologies:

- Two Transistor Forward
- Half Bridge and Full Bridge

Notes ^① through ^⑤ are on page 10

www.irf.com

IRF830AS/L

International
IR Rectifier

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	500	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.60	—	V/°C	Reference to 25°C, I _D = 1mA ^⑥
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	1.4	Ω	V _{GS} = 10V, I _D = 3.0A ^④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.5	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	25 250	μA	V _{DS} = 500V, V _{GS} = 0V V _{DS} = 400V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -30V

Dynamic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	2.8	—	—	S	V _{DS} = 50V, I _D = 3.0A ^⑥
Q _g	Total Gate Charge	—	—	24	nC	I _D = 5.0A V _{DS} = 400V V _{GS} = 10V, See Fig. 6 and 13 ^{④⑥}
Q _{gs}	Gate-to-Source Charge	—	—	6.3		
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	11		
t _{d(on)}	Turn-On Delay Time	—	10	—	ns	V _{DD} = 250V I _D = 5.0A R _G = 14Ω R _D = 49Ω, See Fig. 10 ^{④⑥}
t _r	Rise Time	—	21	—		
t _{d(off)}	Turn-Off Delay Time	—	21	—		
t _f	Fall Time	—	15	—		
C _{iss}	Input Capacitance	—	620	—	pF	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz, See Fig. 5 V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz V _{GS} = 0V, V _{DS} = 400V, f = 1.0MHz V _{GS} = 0V, V _{DS} = 0V to 400V ^{⑤⑥}
C _{oss}	Output Capacitance	—	93	—		
C _{rss}	Reverse Transfer Capacitance	—	4.3	—		
C _{oss}	Output Capacitance	—	886	—		
C _{oss}	Output Capacitance	—	27	—		
C _{oss eff.}	Effective Output Capacitance	—	39	—		

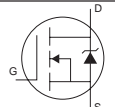
Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ^{②⑥}	—	230	mJ
I _{AR}	Avalanche Current ^{①⑥}	—	5.0	A
E _{AR}	Repetitive Avalanche Energy ^①	—	7.4	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.7	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mounted, steady-state)*	—	40	

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	5.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ^①	—	—	20		
V _{SD}	Diode Forward Voltage	—	—	1.5	V	T _J = 25°C, I _S = 5.0A, V _{GS} = 0V ^④
t _{rr}	Reverse Recovery Time	—	430	650	ns	T _J = 25°C, I _F = 5.0A
Q _{rr}	Reverse Recovery Charge	—	2.0	3.0	μC	di/dt = 100A/μs ^{④⑥}
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

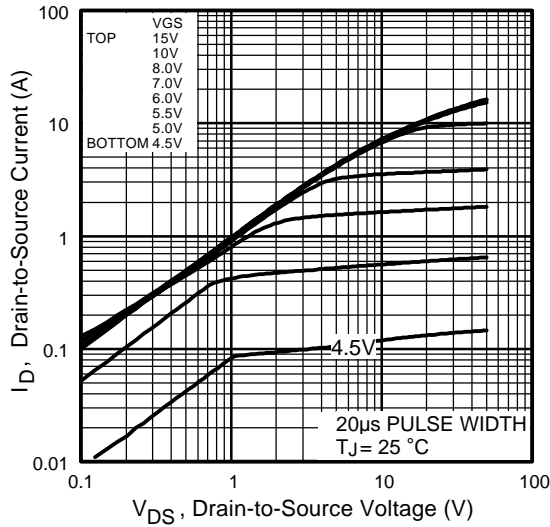


Fig 1. Typical Output Characteristics

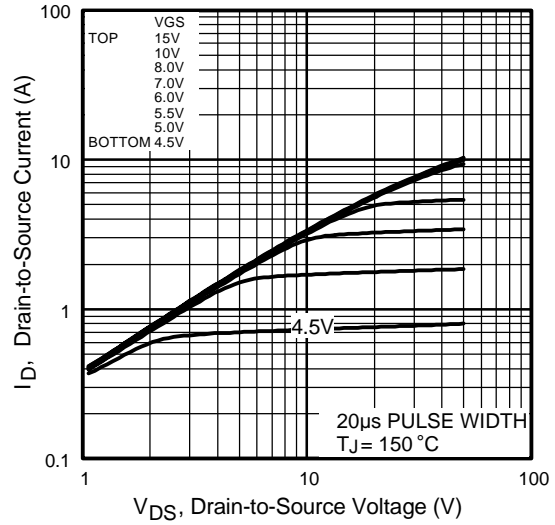


Fig 2. Typical Output Characteristics

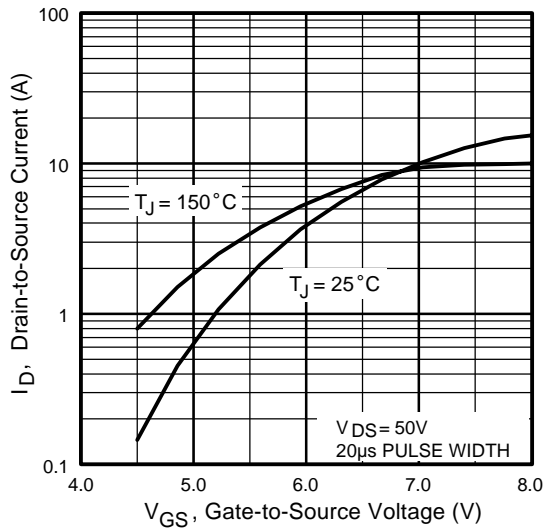


Fig 3. Typical Transfer Characteristics

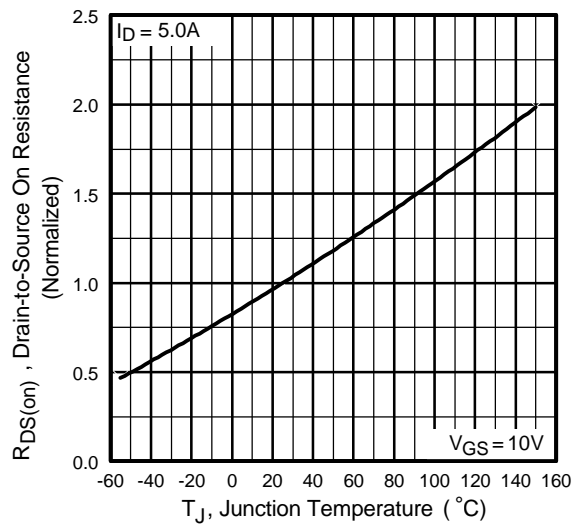


Fig 4. Normalized On-Resistance Vs. Temperature

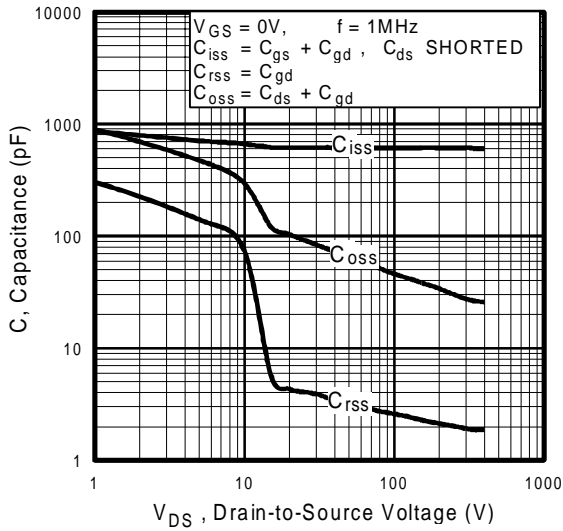


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

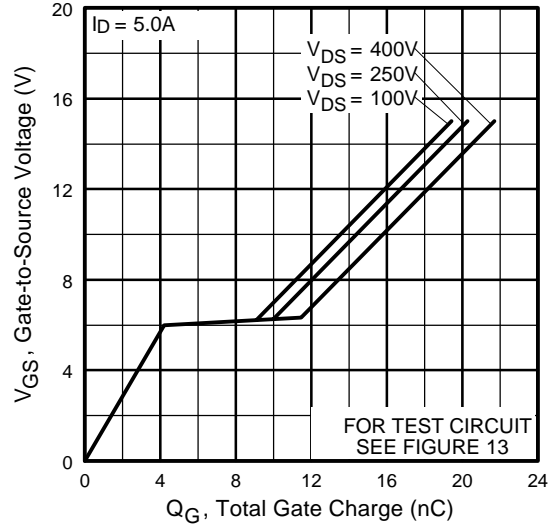


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

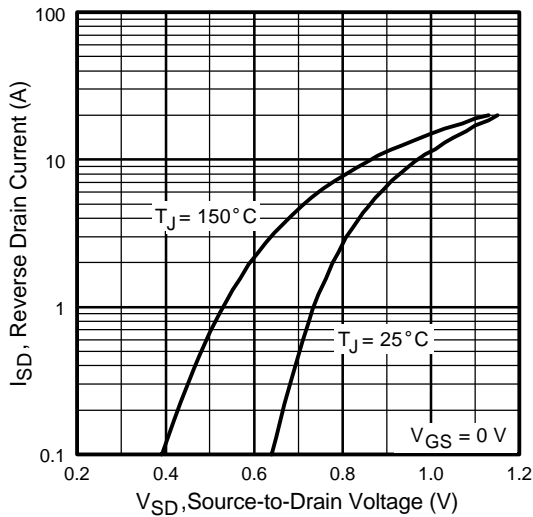


Fig 7. Typical Source-Drain Diode Forward Voltage

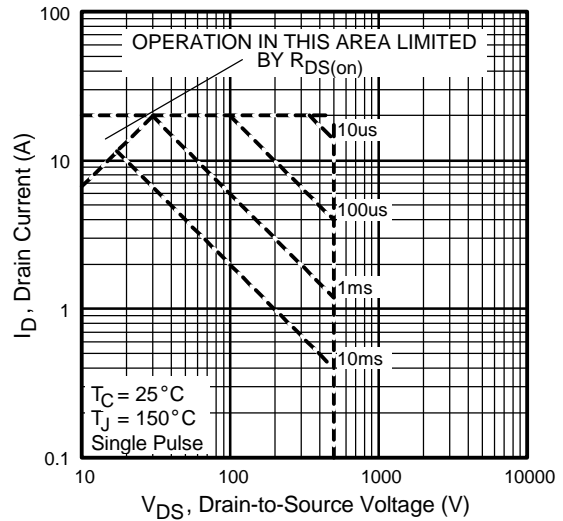


Fig 8. Maximum Safe Operating Area

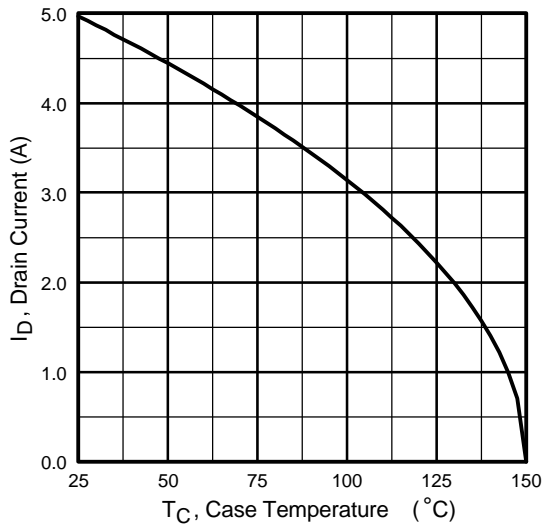


Fig 9. Maximum Drain Current Vs. Case Temperature



Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

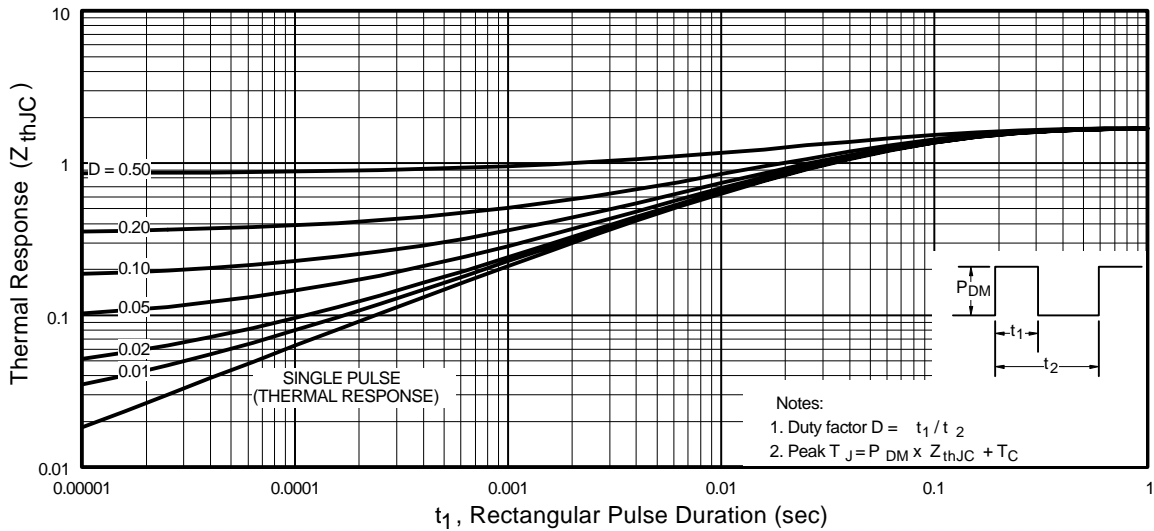


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRF830AS/L

International
IR Rectifier



Fig 12a. Unclamped Inductive Test Circuit



Fig 12b. Unclamped Inductive Waveforms



Fig 13a. Basic Gate Charge Waveform



Fig 13b. Gate Charge Test Circuit

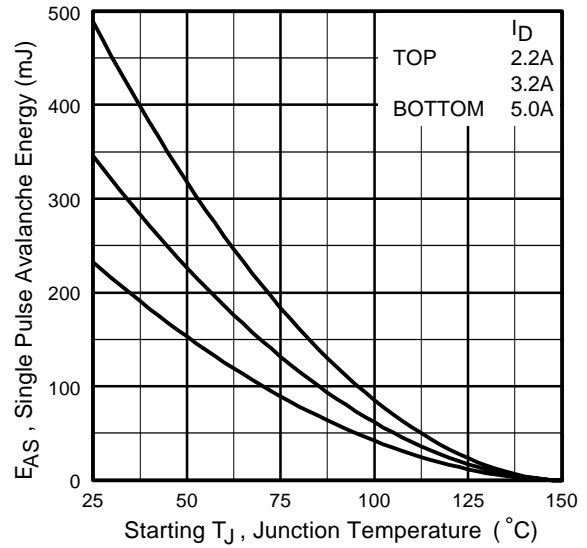


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

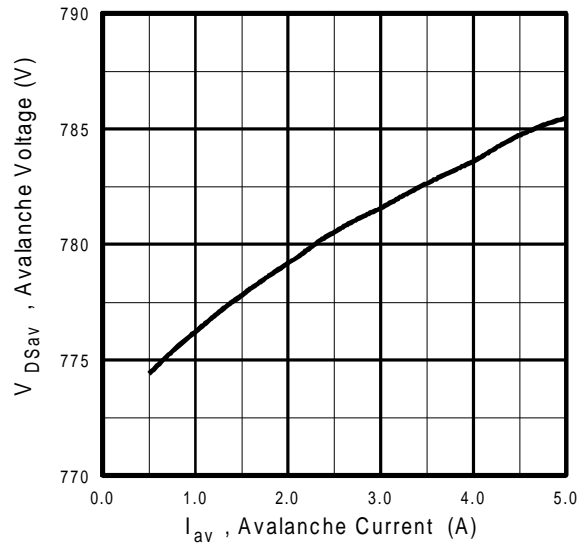


Fig 12d. Typical Drain-to-Source Voltage Vs. Avalanche Current

Peak Diode Recovery dv/dt Test Circuit



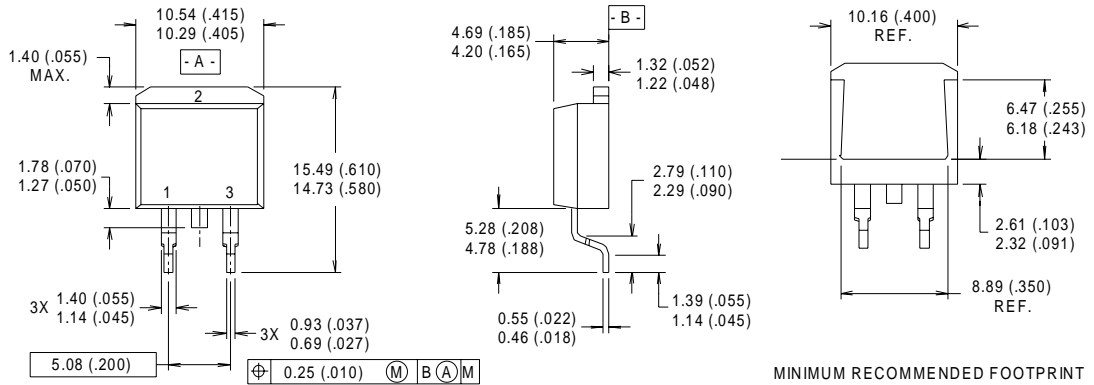
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFET

IRF830AS/L

International
IR Rectifier

D²Pak Package Outline



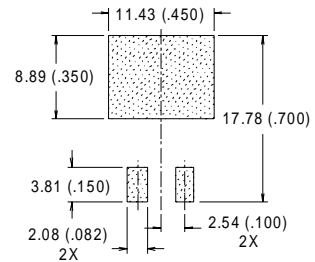
NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS

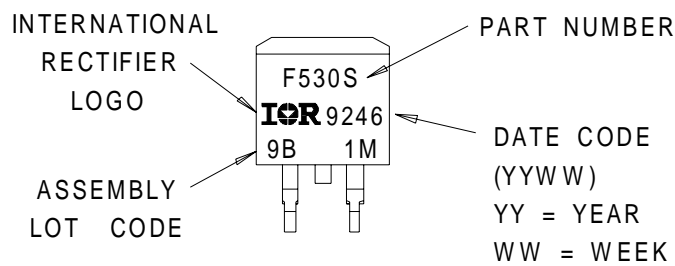
- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

MINIMUM RECOMMENDED FOOTPRINT



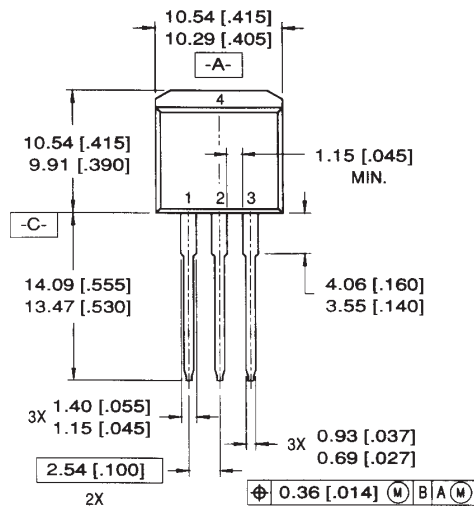
Part Marking Information

D²Pak



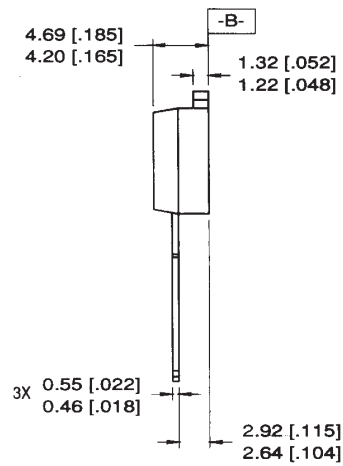
Package Outline

TO-262 Outline



LEAD ASSIGNMENTS

- | | |
|-----------|------------|
| 1 = GATE | 3 = SOURCE |
| 2 = DRAIN | 4 = DRAIN |



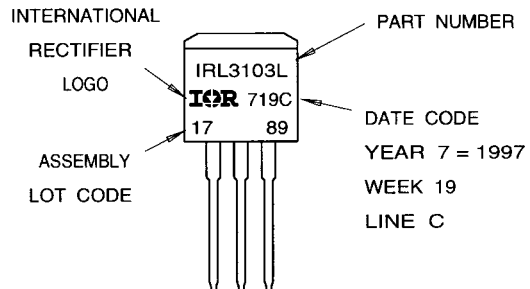
NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

Part Marking Information

TO-262

EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"

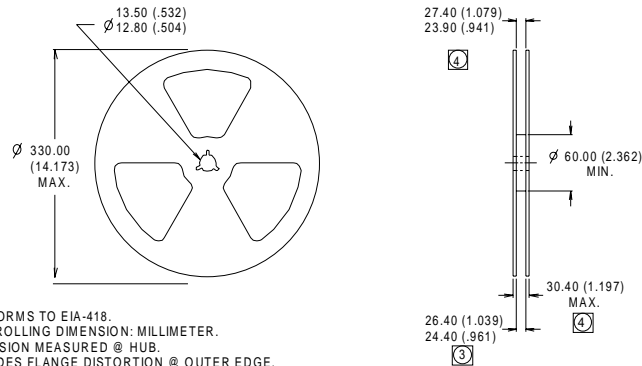
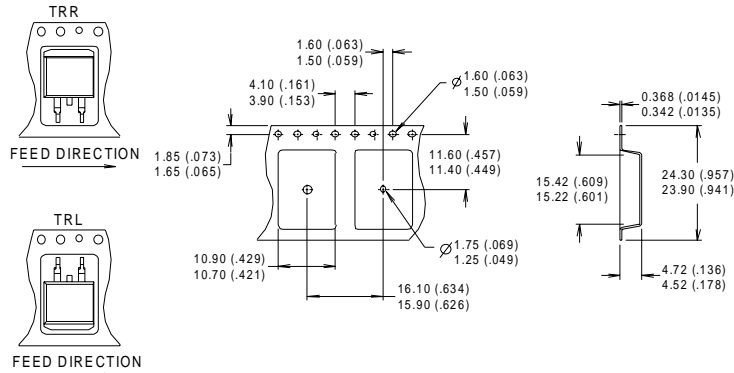


IRF830AS/L

International
IR Rectifier

Tape & Reel Information

D²Pak



- NOTES:
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 18\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 5.0\text{A}$. (See Figure 12)
- ③ $I_{SD} \leq 5.0\text{A}$, $di/dt \leq 370\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
- ⑥ Uses IRF830A data and test conditions

* When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

IR EUROPEAN REGIONAL CENTRE: 439/445 Godstone Rd, Whyteleafe, Surrey CR3 OBL, UK Tel: ++ 44 (0)20 8645 8000

IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111

IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630

IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936

Data and specifications subject to change without notice. 5/00